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DESCRIPTION

ISHA

The DG9051, DG9052, DG9053 are low-voltage monolithic CMOS analog switches and multiplexers. DG9051 is an 8-channel multiplexer; DG9052 is a dual 4 channel multiplexer; and DG9053 is a triple single-pole/double throw (SPDT) switch.

They are designed to operate from a + 2.7 V to + 12 V single supply or \pm 2.7 V to \pm 6 V dual power supplies. All control logic inputs have guaranteed 2 V logic high/0.8 V logic low when operating from a single 5 V or dual \pm 5 V supplies, and 2.4 V logic high/0.8 V logic low when V + = 12 V.

Built on Vishay Siliconix's proprietary high-density process, the DG9051, DG9052, DG9053 offer the advantage of bi-directional signal, rail to rail analog signal handling.

As a committed partner to the community and the environment, Vishay Siliconix manufactures this product with the Lead (Pb)-Free device terminations. For analog switching products manufactured with 100 % matter tin device termination, the Lead (Pb)-free "-E3" suffix is being used as a de-signator.

FEATURES

- Halogen-free according to IEC 61249-2-21 Definition
- 2.7 V to 12 V single supply or ± 2.7 V to ± 6 V dual aupply operation
- Guaranteed R_{ON} matching
- Low Voltage CMOS Logic Compatible
- Compliant to RoHS Directive 2002/95/EC

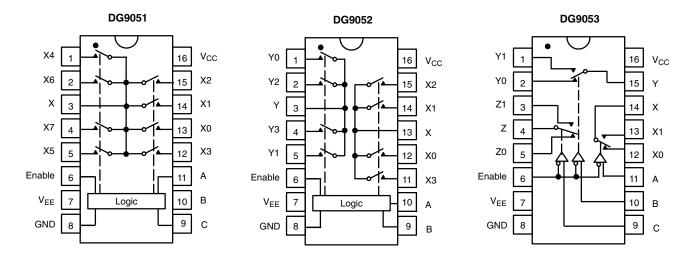
BENEFITS

- Wide operation voltage range
- Pin compatible with 74HC4051/2/5
- Guaranteed low leakage

APPLICATIONS

- Battery powered equipment
- Test process equipment
- Communication systems
- A/V and mixed signal routing
- Automotive

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



ORDERING INFORMATION							
Temp. Range	Package	Part Number					
		DG9051DQ-T1-E3					
- 40 °C to 85°C	TSSOP-16 DG9052D	DG9052DQ-T1-E3					
		DG9053DQ-T1-E3					

The information shown here is a preliminary product proposal, not a commercial product data sheet. Siliconix is not committed to produce this or any similiar product. This information should not be used for design purposes, nor construed as an offer to furnish or sell such products.

Document Number: 73410 S11-1066-Rev. B, 30-May-11



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RUTH TAE Enable		Select Inputs		On Switches			
Input	C*	В	Α	DG9051	DG9052	DG9053	
Н	Х	Х	Х	All switches open	All switches open	All switches open	
L	L	L	L	X - X0	X - X0, Y - Y0	X - X0, Y - Y0, Z - Z0	
L	L	L	Н	X - X1	X - X1, Y - Y1	X - X1, Y - Y0, Z - Z0	
L	L	Н	L	X - X2	X - X2, Y - Y2	X - X0, Y - Y1, Z - Z0	
L	L	Н	Н	X - X3	X - X3, Y - Y3	X - X1, Y - Y1, Z - Z0	
L	н	L	L	X - X4	X - X0, Y - Y0	X - X0, Y - Y0, Z - Z1	
L	н	L	Н	X - X5	X - X1, Y - Y1	X - X1, Y - Y0, Z - Z1	
L	н	Н	L	X - X6	X - X2, Y - Y2	X - X0, Y - Y1, Z - Z1	
L	н	Н	Н	X - X7	X - X3, Y - Y3	X - X1, Y - Y1, Z - Z1	

X = Don't care

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)							
Parameter		Limit	Unit				
Voltage Referenced to V-	V +	13.5					
voltage helefended to v-	GND	7	V				
Digital Inputs ^a	V _S , V _D (V -) - 0.3 to (V +) + 0.3						
Current (Any Terminal Except S or D)	30						
Continuous Current, S or D	100	mA					
Peak Current, S or D (Pulsed at 1 ms, 10 % Duty Cycle Max.)		200					
Package Solder Reflow Conditions ^b IR/Convection		260	°C				
Storage Temperature		- 65 to 150					
Power Dissipation (Packages) ^c	pation (Packages) ^c $T_A = 70 \text{ °C}, \text{TSSOP-16}^d$ 925		mW				



SPECIFICATIONS (Single Supply 12 V)								
Parameter	Symbol	Test Condition Unless Otherwise Specified $V + = 12 V, \pm 10 \%, V = 0 V$		Limits - 40 °C to 8		5°C		
		$V_{A}, V_{\overline{EN}} = 0.8 V \text{ or } 2.4 V^{f}$	Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit	
Analog Switch								
Analog Signal Range ^e	V _{ANALOG}		Full	0		12	V	
On-Resistance	R _{ON}	$V_D = 3.5 V$, $I_S = 1 mA$ Sequence Each Switch On	Room Full		30	40 50	Ω	
R _{ON} Match Between Channels ^g	ΔR_{ON}	V _D = 3.5 V, I _S = 1 mA	Room			5		
Switch Off Leakage Current	I _{S(off)}	V _{EN} = 2.4 V, V _D = 11 V or 1 V, V _S = 1 V or 11 V	Room Full	- 1 - 20		1 20		
Switch On Leakage Suitchic	I _{D(off)}	VEN - 2.1 1, VD - 11 V OI 1 V, VS - 1 V OI 11 V	Room Full	- 1 - 20		1 20	nA	
Channel On Leakage Current	I _{D(on)}	$V_{\overline{EN}} = 0 V, V_S = V_D = 1 V \text{ or } 11 V$	Room Full	- 2 - 10		2 10		
Digital Control				1	•	1		
Logic High Input Voltage	V _{INH}		Full	2.4			V	
Logic Low Input Voltage	V _{INL}		Full			0.8	•	
Input Current	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2.4 \text{ V or } 0.8 \text{ V}$	Full	- 1		1	μΑ	
Dynamic Characteristics			1	1	1			
Transition Time	t _{TRANS}	$V_{NO}/V_{NC} = 8 V/0 V, 0 V/8 V$ $R_{L} = 300 \Omega, C_{L} = 35 pF$	Room Full		26	35 55		
Break-Before-Make Time	t _{BBM}		Room Full	3	10		ns	
Enable Turn-On Time	$t_{ON(\overline{EN})}$	$V_{X,Y,Z} = 5 V, V_S = 0 V,$ $R_L = 306 \Omega, C_L = 35 pF$	Room Full		20	35 45		
Enable Turn-Off Time	$t_{\text{OFF}(\overline{\text{EN}})}$		Room Full		16	30 40		
Charge Injection ^e	Q	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		38		рС	
Off-Isolation ^{e,h}	OIRR	f = 1 MHz, R ₁ = 50 Ω	Room		- 78		dB	
Crosstalk ^e	X _{TALK}	r = r m n z, n = 50 s z	Room		- 83		uБ	
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V_S = 0 V, $V_{\overline{EN}}$ = 2.4 V Room 4		4				
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 2.4 \text{ V}$	Room		8		pF	
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 0 \text{ V}$	Room		15			
Power Supply								
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V+$	Room			1	μA	

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SPECIFICATIONS (Dua	al Supply	V + = 5 V, V - = - 5 V)					
Parameter	Symbol	Test Condition Unless Otherwise Specified		Limits - 40 °C to 85°C			
	•,	V + = 5 V, V - = - 5 V ± 10 % V _A , V _{EN} = 0.8 V or 2 V ^f	Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	- 5		5	V
On-Resistance	R _{ON}	V + = 4.5 V, V - = - 4.5 V, V _D = \pm 3 V, I _S = 1 mA Sequence Each Switch On	Room Full		35	55 60	
R _{ON} Match Between Channels ^g	ΔR_{ON}		Room			5	Ω
On-Resistance Flatness ⁱ	R _{ON} Flatness	V + = 4.5 V, V - = - 4.5 V, V _D = \pm 3 V, I _S = 1 mA	Room		7	10	
Switch Off Leakage Current ^a	I _{S(off)}	V + = 5.5 V, V - = - 5.5 V	Room Full	- 1 - 20		1 20	
Switch Off Leakage Current	I _{D(off)}	$V_{\overline{EN}} = 2 V, V_{D} = \pm 4 .5 V, V_{S} = \pm 4.5 V$		- 1 - 20		1 20	nA
Channel On Leakage Current ^a	I _{D(on)}	V + = 5.5 V, V - = - 5.5 V V _{EN} = 0 V, V _D = \pm 4.5 V, V _S = \pm 4.5 V	Room Full	- 2 - 10		2 10	
Digital Control							
Logic High Input Voltage	V _{INH}		Full	2			v
Logic Low Input Voltage	V _{INL}		Full			0.8	
Input Current ^a	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2 V \text{ or } 0.8 V$	Full	- 1		1	μΑ
Dynamic Characteristics							
Transition Time ^e	t _{TRANS}	$V += 4.5 V, V -= -4.5 V V_{NO/NC} = \pm 3 V, \\ R_L = 300 \ \Omega, \ C_L = 35 \ pF$	Room Full		35	50 65	
Break-Before-Make Time ^e	t _{BBM}		Room Full	5	12		ns
Enable Turn-On Time ^e	t _{ON(EN)}	$V_{X,Y, Z} = +/- 3 V, V_S = 0 V,$ $R_L = 300 \Omega, C_L = 35 pF$	Room Full		38	55 70	110
Enable Turn-Off Time ^e	$t_{OFF(\overline{EN})}$		Room Full		22	35 50	
Source Off Capacitance ^e	C _{S(off)}	$f = 1 \text{ MHz}, \text{ V}_{S} = 0 \text{ V}, \text{ V}_{\overline{EN}} = 2 \text{ V}$	Room		5		
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 2 \text{ V}$	Room		9		pF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 0 \text{ V}$	Room		13		
Power Supply							-
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V +$	Room			1	μA
	I-	- En A	Room	- 1			



SPECIFICATIONS (Single Supply 5 V)							
Parameter	Symbol	Test Condition Unless Otherwise Specified V + = 5 V, ± 10 %, V - = 0 V		Limits - 40 °C to 85°C			-
		$V_{A}, V_{\overline{EN}} = 0.8 V \text{ or } 2 V^{f}$	Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		5	V
On-Resistance	R _{ON}	V + = 4.5 V, V _D or V _S = 3 V or 3.5 V, I _S = 1 mA	Room Full		80	100 120	Ω
R _{ON} Match Between Channels ^g	ΔR_{ON}	$V + = 4.5 V$, $V_D = 3 V$, $I_S = 1 mA$	Room			8	
Switch Off Leakage Current ^a	I _{S(off)}	V + = 5.5 V, V _{EN} = 2 V	Room Full	- 1 - 20		1 20	
Switch On Leakage Current	I _{D(off)}	$V_{\rm S}$ = 1 V or 4.5 V, $V_{\rm D}$ = 4.5 V or 1 V	Room Full	- 1 - 20		1 20	nA
Channel On Leakage Current ^a	I _{D(on)}	V + = 5.5 V, V _{EN} = 0 V V _D = V _S = 1 V or 4.5 V	Room Full	- 2 - 10		2 10	
Digital Control	•		•		•		
Logic High Input Voltage	V _{INH}		Full	2			V
Logic Low Input Voltage	V _{INL}		Full			0.8	v
Input Current ^a	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2 V \text{ or } 0.8 V$	Full	- 1		1	μA
Dynamic Characteristics							
Transition Time	t _{TRANS}	$V + = 4.5 V, V - = 0 V, V_{NO / NC} = 3 V / 0 V, 0 V / 3 V, R_L = 300 \Omega, C_L = 35 pF$	Room		40		
Break-Before-Make Time	t _{BBM}		Room		15		ns
Enable Turn-On Time	$t_{ON(\overline{EN})}$	V + = 4.5 V, V _{X,Y,Z} = 3 V, V _S = 0 V, R _L = 300 Ω, C _L = 35 pF	Room		40		
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$	··· [000, 0 [00 p.	Room		20		
Charge Injection ^e	Q	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		20		рС
Off-Isolation ^{e,h}	OIRR	f = 1 MHz, R ₁ = 50 Ω	Room		- 79		dB
Crosstalk ^e	X _{TALK}				- 83		uв
Source Off Capacitance ^e	C _{S(off)}	$f = 1 \text{ MHz}, \text{ V}_{\text{S}} = 0 \text{ V}, \text{ V}_{\overline{\text{EN}}} = 0 \text{ V}$ Room			4		
Drain Off Capacitance ^e	C _{D(off)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 2 \text{ V}$	Room		8		pF
Drain On Capacitance ^e	C _{D(on)}	$f = 1 \text{ MHz}, V_D = 0 \text{ V}, V_{\overline{EN}} = 0 \text{ V}$	Room		15		
Power Supply							
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V +$	Room			1	μA

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Parameter	Test Condition Unless Otherwise Specified			Limits - 40 °C to 85°C			
		V + = 3 V, ± 10 %, V - = 0 V V _{EN} = 0.4 V or 2 V	Temp. ^b	Min. ^c	Typ. ^d	Max. ^c	Unit
Analog Switch							
Analog Signal Range ^e	V _{ANALOG}		Full	0		3	V
On-Resistance	R _{ON}	V + = 2.7 V, V_D = 1.5 V, I_S = 0.1 mA	Room		130		0
R _{ON} Match Between Channels ^g	ΔR_{ON}	V + = 2.7 V, V_D = 1.5 V, I_S = 0.1 mA	Room			12	Ω
	I _{S(off)}	V + = 3.3 V, V _{EN} = 2 V	Room Full	- 1 - 20		1 20	
Switch Off Leakage Current ^a	I _{D(off)}	V_{S} = 3 or 0.3 V, V_{D} = 0.3 or 3 V	Room Full	- 1 - 20		1 20	nA
Channel On Leakage Current ^a	I _{D(on)}	V + = 3.3 V, V _{EN} = 0 V V _S = 3 or 0.3 V, V _D = 0.3 or 3 V	Room Full	- 2 - 10		2 10	
Digital Control			<u> </u>				
Logic High Input Voltage	V _{INH}		Full	2			v
Logic Low Input Voltage	V _{INL}		Full			0.4	v
Input Current ^a	I _{IN}	$V_{AX} = V_{\overline{EN}} = 2 V \text{ or } 0.4 V$	Full	- 1		1	μA
Dynamic Characteristics							
Transition Time	t _{TRANS}	V + = 2.7 V, V _{NO/NC} = 1.5 V/0 V, 0 V/1.5 V R _L = 300 $\Omega,$ C _L = 35 pF	Room		80		
Break-Before-Make Time	t _{BBM}	V + = 2.7 V, V _{X,Y,Z} = 1.5 V, V _S = 0 V,	Room Full	5	25		ns
Enable Turn-On Time	t _{ON(EN)}	$R_L = 300 \Omega, C_L = 35 pF$	Room		90		
Enable Turn-Off Time	$t_{OFF(\overline{EN})}$		Room		30		
Charge Injection ^e	Q	C_L = 1 nF, V_{GEN} = 0 V, R_{GEN} = 0 Ω	Room		9		рС
Off-Isolation ^{e,h}	OIRR	$f = 1 MHz, R_1 = 50 \Omega$	Room		- 78		dB
Crosstalk ^e	X _{TALK}	$r = r m r z, n_L = 50 sz$	Room		- 83		uБ
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz, V_S = 0 V, $V_{\overline{EN}}$ = 1.8 V	Room		5		
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz, V_D = 0 V, $V_{\overline{EN}}$ = 1.8 V	Room		10		pF
Drain On Capacitance ^e	C _{D(on)}			15			
Power Supply							
Power Supply Current	l+	$V_{\overline{EN}} = V_A = 0 V \text{ or } V +$	Room			1	μA

Notes:

a. Leakage parameters are guaranteed by worst case test condition and not subject to production test.

b. Room = 25°C, Full = as determined by the operating temperature suffix.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

d. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

e. Guaranteed by design, not subject to production test.

f. V_{IN} = input voltage to perform proper function.

g. $\Delta R_{DON} = R_{DON} Max - R_{DON} Min.$

h. Worst case isolation occurs on Channel 4 due to proximity to the drain pin.

i. R_{DON} flatness is measured as the difference between the minimum and maximum measured values across a defined Analog signal.

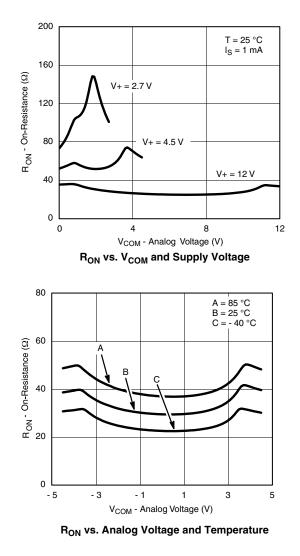
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

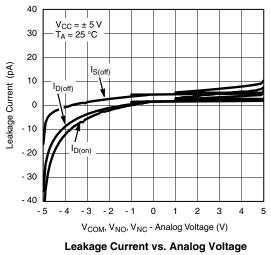
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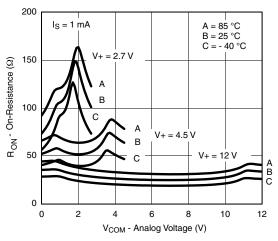


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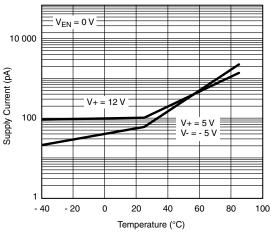




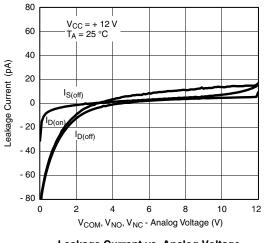




R_{ON} vs. Analog Voltage and Temperature



Supply Current vs. Temperature



Leakage Current vs. Analog Voltage

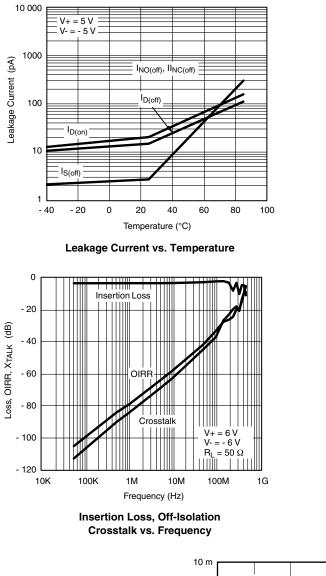
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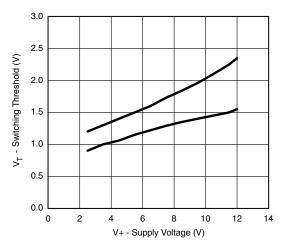
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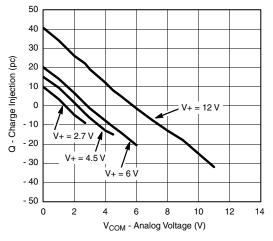


TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)

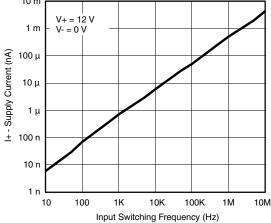




Switching Threshold vs. Supply Voltage



Charge Injection vs. Analog Voltage

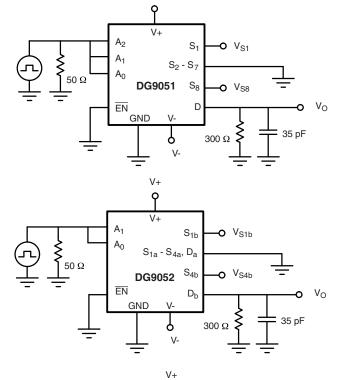


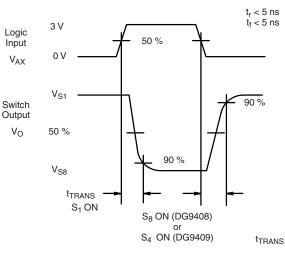
Supply Current vs. Input Switching Frequency



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TEST CIRCUITS





Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V



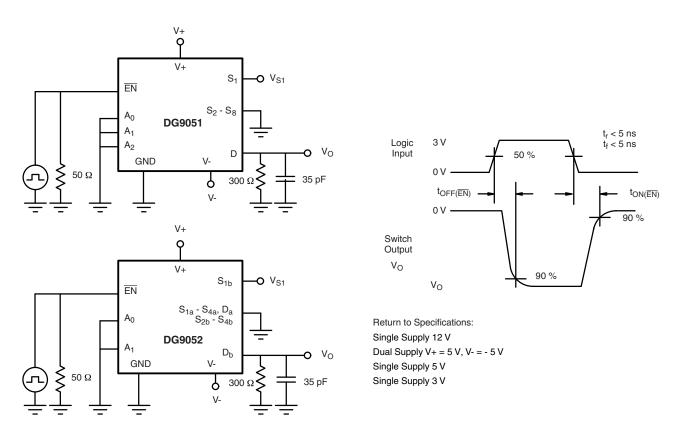


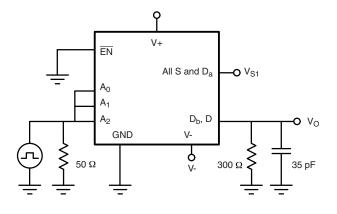
Figure 2. Enable Switching Time

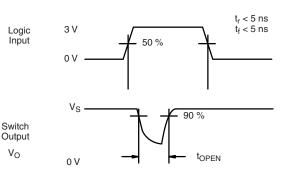
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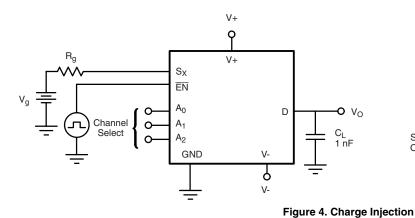
TEST CIRCUITS

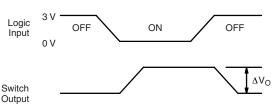




Return to Specifications: Single Supply 12 V Dual Supply V+ = 5 V, V- = - 5 V Single Supply 5 V Single Supply 3 V

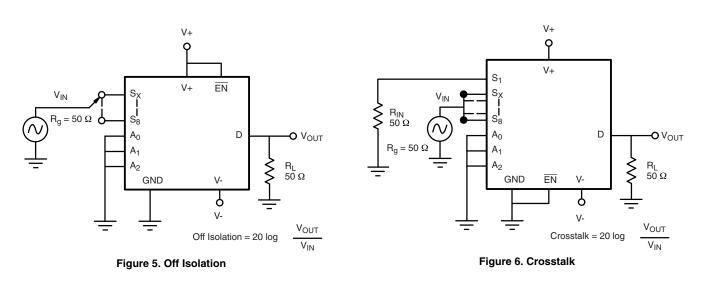






 ΔV_O is the measured voltage due to charge transfer error Q, when the channel turns off.

 $\mathsf{Q}=\mathsf{C}_\mathsf{L} \mathrel{x} \Delta\mathsf{V}_\mathsf{O}$



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TEST CIRCUITS

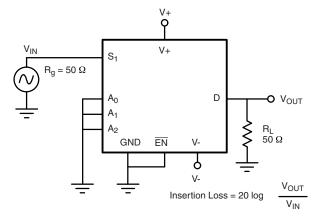


Figure 7. Insertion Loss

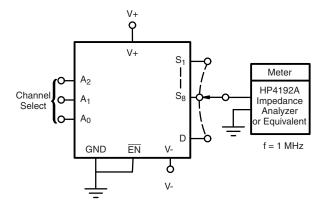


Figure 8. Source Drain Capacitance

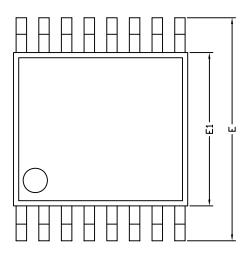
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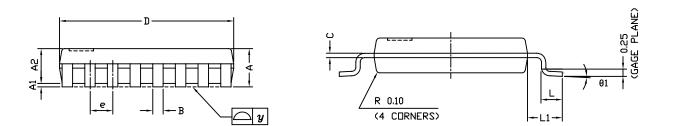


Package Information

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TSSOP: 16-LEAD





	DIMENSIONS IN MILLIMETERS						
Symbols	Min	Nom	Мах				
A	-	1.10	1.20				
A1	0.05	0.10	0.15				
A2	-	1.00	1.05				
В	0.22	0.28	0.38				
С	-	0.127	-				
D	4.90	5.00	5.10				
E	6.10	6.40	6.70				
E1	4.30	4.40	4.50				
е	-	0.65	-				
L	0.50	0.60	0.70				
L1	0.90	1.00	1.10				
у	-	-	0.10				
θ1	0°	3°	6°				
ECN: S-61920-Rev. D, 23 DWG: 5624	-Oct-06						



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